



DMN95H8D5HCTI

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on)	Package	I _{D MAX} T _C = +25°С
950V	$7\Omega@V_{GS} = 10V$	ITO220AB (Type TH)	2.5A

Description

This new generation complementary dual MOSFET features low onresistance and fast switching, making it ideal for high efficiency power management applications.

Applications

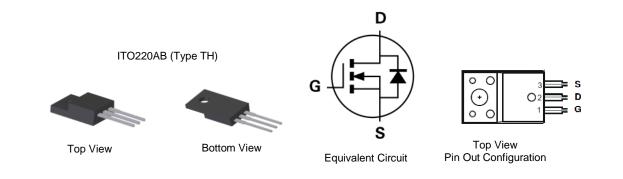
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: ITO220AB (Type TH)
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN95H8D5HCTI	ITO220AB (Type TH)	50 Pieces/Tube

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at t https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	950	V
Gate-Source Voltage		V _{GSS}	±30	V
Continuous Drain Current (Notes 5) V _{GS} = 10V	T _C = +25°C T _C = +100°C	ID	2.5 1.5	А
Pulsed Drain Current (Note 6)		I _{DM}	3	A
Avalanche Current, L = 60mH (Note 7)		I _{AS}	1.8	A
Avalanche Energy, L = 60mH (Note 7)		E _{AS}	97	mJ
Peak Diode Recovery dv/dt (Note 7)		dv/dt	3.3	V/ns

Thermal Characteristics

Characteristic		Symbol	Мах	Unit
Power Dissipation (Note 5)	T _C = +25°C T _C = +100°C	PD	30 12	W
Thermal Resistance, Junction to Case (Note 5)	T _C = +25°C	R _{θJC}	4.2	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

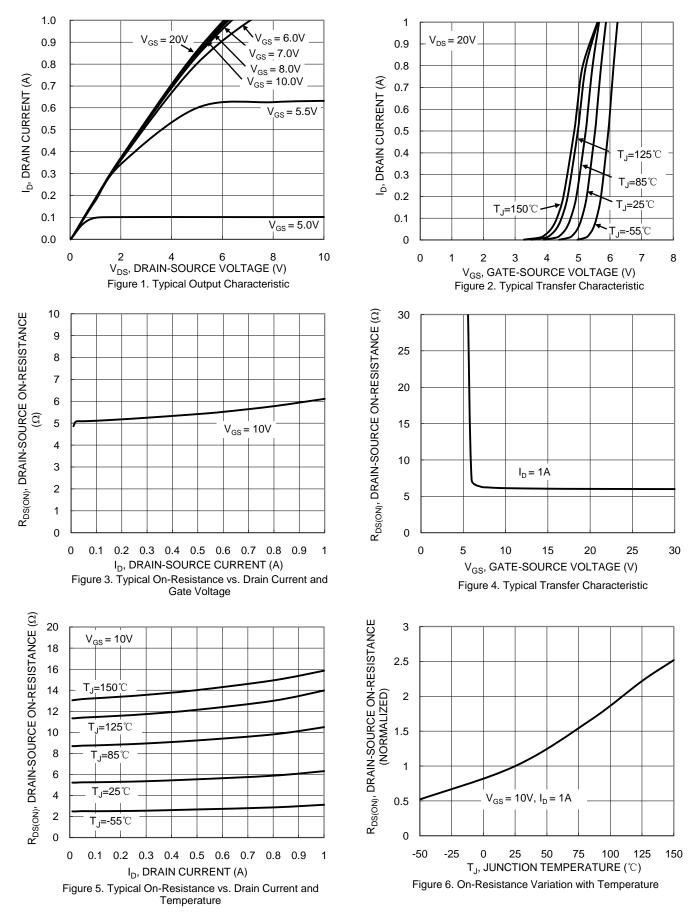
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	1 - 1					
Drain-Source Breakdown Voltage	BV _{DSS}	950			V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	$V_{DS} = 950V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}		5.5	7.0	Ω	$V_{GS} = 10V, I_D = 1A$
Diode Forward Voltage	V _{SD}		—	1.2	V	$V_{GS} = 0V, I_S = 2A$
DYNAMIC CHARACTERISTICS (Note 7)				-		
Input Capacitance	Ciss		470		pF	$\label{eq:VDS} \begin{array}{l} V_{DS} = 25V, f = 1.0MHz, \\ V_{GS} = 0V \end{array}$
Output Capacitance	Coss		45	—		
Reverse Transfer Capacitance	C _{rss}	_	0.6	_		
Gate Resistance	Rg		1.2		Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	tal Gate Charge Q _a — 7.9 —					
Gate-Source Charge	Q _{gs}	_	2.5		nC	$V_{DD} = 720V, I_D = 2A,$ $V_{GS} = 10V$
Gate-Drain Charge	Q _{gd}		2.9			
Turn-On Delay Time	t _{D(ON)}		16			
Turn-On Rise Time	t _R	_	21	_		$\label{eq:VDD} \begin{array}{l} V_{DD} = 450V, \ R_{g} = 25\Omega, \ I_{D} = 2A, \\ V_{GS} = 10V \end{array}$
Turn-Off Delay Time	t _{D(OFF)}	_	17.6	_	ns	
Turn-Off Fall Time	tF		17			
Body Diode Reverse Recovery Time	t _{RR}		375		ns	dl/dt = 100A/µs, V _{DS} = 100V,
Body Diode Reverse Recovery Charge	Q _{RR}	_	2.9	_	μC	$I_F = 2A$

Notes: 5. Device mounted on infinite heatsink.

bevice mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Guaranteed by design. Not subject to production testing.
Short duration pulse test used to minimize self-heating effect.



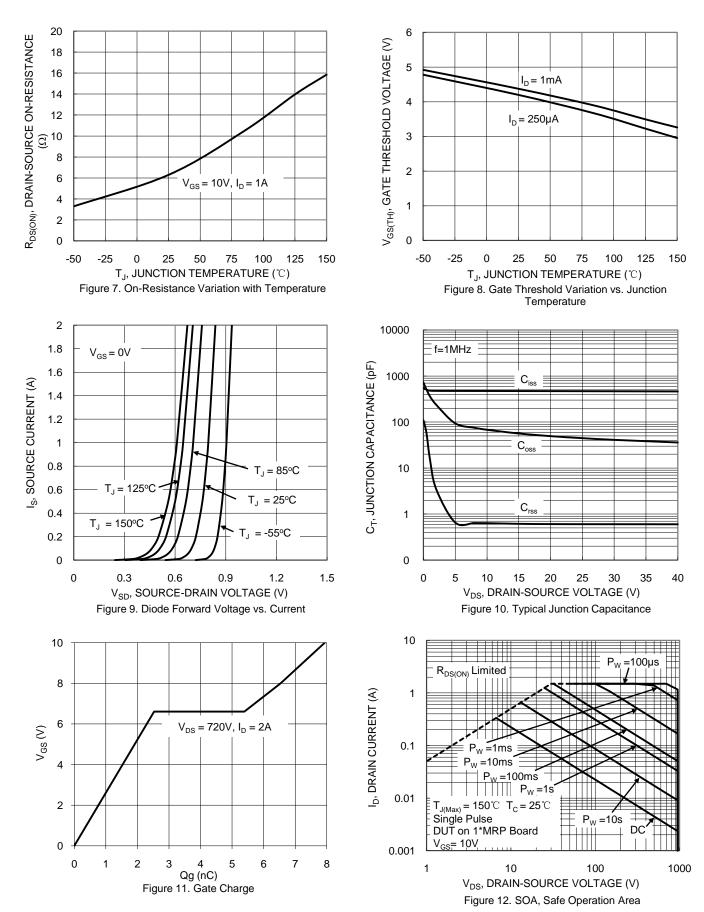
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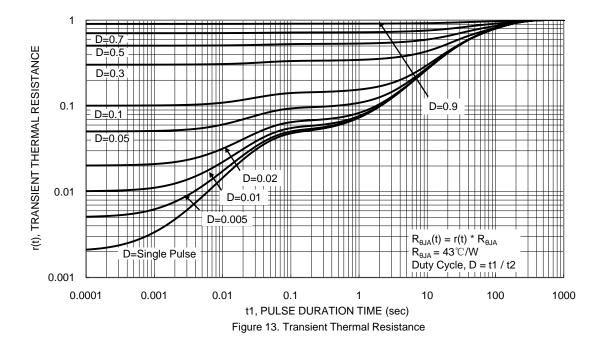


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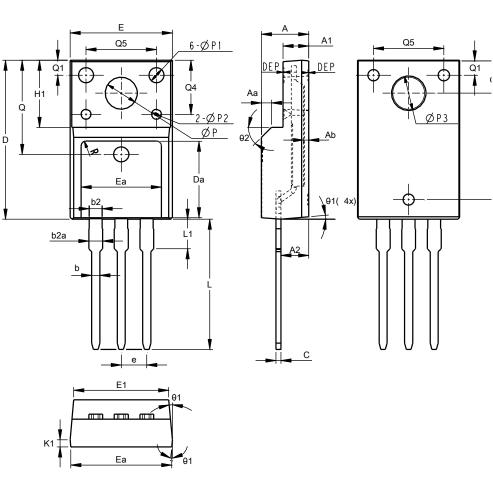






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



ITO220AB (Type TH)						
Dim	Min	Max	Тур			
Α	4.50	4.90	4.70			
A1	2.34	2.74	2.54			
A2	2.63	2.89	2.76			
Aa		1.00 RE				
Ab	0.30	0.60	0.56			
b	0.75	0.90	0.80			
b2	1.23	1.38	1.28			
b2a	1.25	1.45	1.35			
С	0.45	0.60	0.50			
D	15.47	16.27	15.87			
Da	7.55	8.05	7.80			
е	2.54 BSC					
Е	9.86	10.46				
E1	9.26	9.66	9.46			
Ea	7.70	8.30	8.00			
Eb	9.76 10.34		10.04			
H1	6.70 REF					
L	12.58	13.38	12.98			
L1	2.81	3.05	2.93			
K1	0.65	0.75	0.70			
Q	-	.40 RE				
Q1	1.00	2.00	1.50			
Q2	13.50	14.30	13.90			
Q3	3.15	3.45	3.30 5.40			
Q4		5.15 5.65				
Q5	6.70					
ØP	3.06	3.40	3.18			
ØP1	1.40	1.60	1.50			
ØP2	0.95	1.05	1.00			
ØP3	3.30	3.60	3.45			
θ1	3°	7°	5⁰			
θ2	-	45°	45° -			
R		.50 RE				
DEP	0.05	0.15	0.10			
All Dimensions in mm						

ITO220AB (Type TH)



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